



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

A1015LT1 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.2 W($T_{amb}=25^{\circ}C$)

MARKING: BA

MAXIMUM RATINGS* $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	150	mA
P_D	Total Device Dissipation	200	mW
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}C$

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -50V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.1	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA$ $f = 30MHz$	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	130-200	200-400

Typical Characteristics

A1015LT1

